NLAS4157

Analog Switch, SPDT, 1 Ω R_{ON}

The NLAS4157 is a low R_{ON} SPDT analog switch. This device is designed for low operating voltage, high current switching of speaker output for cell phone applications. It can switch a balanced stereo output. The NLAS4157 can handle a balanced microphone/speaker/ringtone generator in a monophone mode. The device contains a break−before−make (BBM) feature.

Features

- Single Supply Operation:
  1.65 V to 5.5 V V_{CC}
  Function Directly from LiON Battery
- Tiny SC88 6−Pin Pb−Free Package:
  Meets JEDEC MO−220 Specifications
- R_{ON} Typical = 0.8 Ω @ V_{CC} = 4.5 V
- Low Static Power
- This is a Pb−Free Device

Typical Applications

- Cell Phone Speaker/Microphone Switching
- Ringtone−Chip/Amplifier Switching
- Stereo Balanced (Push−Pull) Switching

Important Information

- Ringtone−Chip/Amplifier Switching
- Continuous Current Rating Through each Switch ±300 mA
- Conforms to: JEDEC MO−220, Issue H, Variation VEED−6
- Pin for Pin Compatible with FSA4157

ON Semiconductor®

http://onsemi.com

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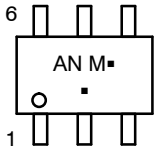
SC−88 (SOT−363)
CASE 419B

MARKING DIAGRAM

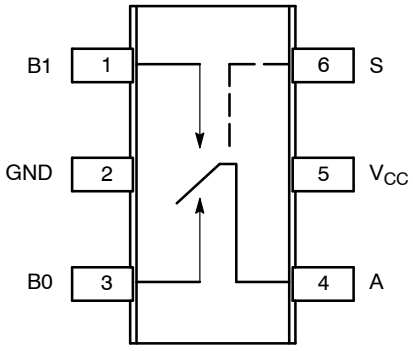


AN = Specific Device Code
M = Date Code*
G = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENTS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

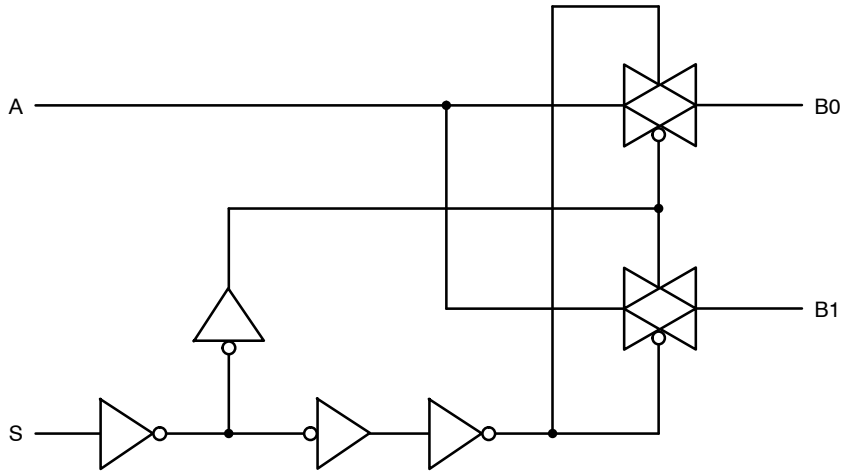


Figure 1. Input Equivalent Circuit

PIN DESCRIPTION

Pin Name	Description
A, B0, B1	Data Ports
S	Control Input

TRUTH TABLE

Control Input	Function
L	B0 Connected to A
H	B1 Connected to A

H = HIGH Logic Level.
L = LOW Logic Level.

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_{CC}	Positive DC Supply Voltage	−0.5 to +6.0	V
V_{IS}	Analog Input Voltage (V_{NO}, V_{NC}, or V_{COM})	−0.5 to V_{CC} +0.5	V
V_{IN}	Digital Select Input Voltage	−0.5 to +6.0	V
I_{anl1}	Continuous DC Current from COM to NC/NO	±300	mA
$I_{anl-pk1}$	Peak Current from COM to NC/NO, 10 Duty Cycles (Note 1)	±500	mA
I_{clmp}	Continuous DC Current into COM/NC/NO with respect to V_{CC} or GND	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
1. Defined as 10% ON, 90% off duty cycle.

RECOMMENDED OPERATING CONDITIONS

Symbol	Rating		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		1.65	5.5	V
V_{IS}	Analog Input Voltage (A, B0, B1)		0	V_{CC}	V
V_{IN}	Digital Select Input Voltage (S)		0	V_{CC}	V
T_A	Operating Temperature Range		−40	85	°C
t_r, t_f	Input Rise or Fall Time, SELECT	V_{CC} = 3.0 V V_{CC} = 5.5 V		20 10	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = +25°C			T_A = −40°C to +85°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	HIGH Level Input Voltage		2.7 4.5				2.0 2.4		V
V_{IL}	LOW Level Input Voltage		2.7 4.5					0.6 0.8	V
I_{IN}	Input Leakage Current	0 ≤ V_{IN} ≤ 5.5 V	0−5.5			±0.1		±1	μA
I_{OFF}	OFF State Leakage Current (Note 7)	0 ≤ A, B ≤ V_{CC}	5.5	−2.0		+2.0		±20	nA
I_{ON}	ON State Leakage Current (Note 7)	0 ≤ A, B ≤ V_{CC}	5.5	−4.0		+4.0		±40	nA
R_{ON}	Switch On Resistance (Note 2)	I_O = −100 mA, B_0 or B_1 = 3.5 V	2.7		2.0	4.0		4.3	Ω
		I_O = −100 mA, B_0 or B_1 = 1.5 V	4.5		0.8	1.15		1.3	
I_{CC}	Quiescent Supply Current All Channels ON or OFF	V_{IN} = V_{CC} or GND, I_{OUT} = 0	5.5			0.5		1.0	μA
Analog Signal Range									
ΔR_{ON}	On Resistance Match Between Channels (Notes 2, 3, 4)	I_A = −100 mA, B_0 or B_1 = 1.5 V I_A = −100 mA, B_0 or B_1 = 3.5 V	2.7 4.5		0.15 0.12			 0.15	Ω
R_{flat}	On Resistance Flatness (Notes 2, 3, 5)	I_A = −100 mA, B_0 or B_1 = 0 V, 0.75 V, 1.5 V I_A = −100 mA, B_0 or B_1 = 0 V, 1.0 V, 2.0 V	2.7 4.5		1.4 0.3			 0.4	Ω

2. Measured by the voltage drop between A and B pins at the indicated current through the switch. On Resistance is determined by the lower of the voltages on the two (A or B Ports).
3. Parameter is characterized but not tested in production.
4. DR_{ON} = R_{ON} max − R_{ON} min measured at identical V_{CC}, temperature and voltage levels.
5. Flatness is defined as the difference between the maximum and minimum value of On Resistance over the specified range of conditions.
6. Guaranteed by Design.
7. This parameter is guaranteed by design but not tested. The bus switch contributes no propagation delay other than the RC delay of the On Resistance of the switch and the 50 pF load capacitance, when driven by an ideal voltage source (zero output impedance).

AC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = +25°C			T_A = −40°C to +85°C		Unit	Figure #
				Min	Typ	Max	Min	Max		
t_{PHL} t_{PLH}	Propagation Delay Bus−to−Bus (Note 9)	V_I = OPEN	2.7 4.5			2.0 0.3			ns	3, 4
t_{ON}	Output Enable Time Turn On Time (A to B_n)	B_0 or B_1 = 1.5 V, R_L = 50 Ω, C_L = 35 pF B_0 or B_1 = 3.0 V, R_L = 50 Ω, C_L = 35 pF	2.7 4.5			30 20		35 25	ns	3, 4
t_{OFF}	Output Disable Time Turn Off Time (A Port to B Port)	B_0 or B_1 = 1.5V, R_L = 50 Ω, C_L = 35 pF B_0 or B_1 = 3.0 V, R_L = 50 Ω, C_L = 35 pF	2.7 4.5			20 15		25 20	ns	3, 4
t_{BBM}	Break Before Make Time (Note 8)		2.7 4.5	0.5 0.5			0.5 0.5		ns	2
Q	Charge Injection (Note 8)	C_L = 1.0 nF, V_{GEN} = 0 V R_{GEN} = 0 Ω	2.7 4.5		26 48				pC	6
O_{IRR}	Off Isolation (Note 10)	R_L = 50 Ω f = 1.0 MHz	2.7 – 5.5		−52				dB	5
X_{talk}	Crosstalk	R_L = 50 Ω f = 1.0 MHz	2.7 – 5.5		−57				dB	7
BW	−3 dB Bandwidth	R_L = 50 Ω	2.7 – 5.5		40				MHz	8
THD	Total Harmonic Distortion (Note 8)	R_L = 600 Ω 0.5 V_{P-P} f = 20 Hz to 20 kHz	2.7 – 5.5		0.012				%	9

8. Guaranteed by Design.
9. This parameter is guaranteed by design but not tested. The bus switch contributes no propagation delay other than the RC delay of the On Resistance of the switch and the 50 pF load capacitance, when driven by an ideal voltage source (zero output impedance).
10. Off Isolation = 20 $\log_{10}$ [V_A/V_{Bn}].

CAPACITANCE (Note 11)

Symbol	Parameter	Test Conditions	Typ	Max	Unit	Figure #
C_{IN}	Select Pin Input Capacitance	V_{CC} = 0 V, f = 1 MHz	10		pF	
C_{IO-B}	B Port Off Capacitance	V_{CC} = 4.5 V, f = 1 MHz	25		pF	
C_{IOA-ON}	A Port Capacitance when Switch is Enabled	V_{CC} = 4.5 V, f = 1 MHz	87		pF	

11. T_A = +25°C, f = 1 MHz, Capacitance is characterized but not tested in production.

DEVICE ORDERING INFORMATION

Device Order Number	Package	Shipping†
NLAS4157DFT2G	SC−88 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

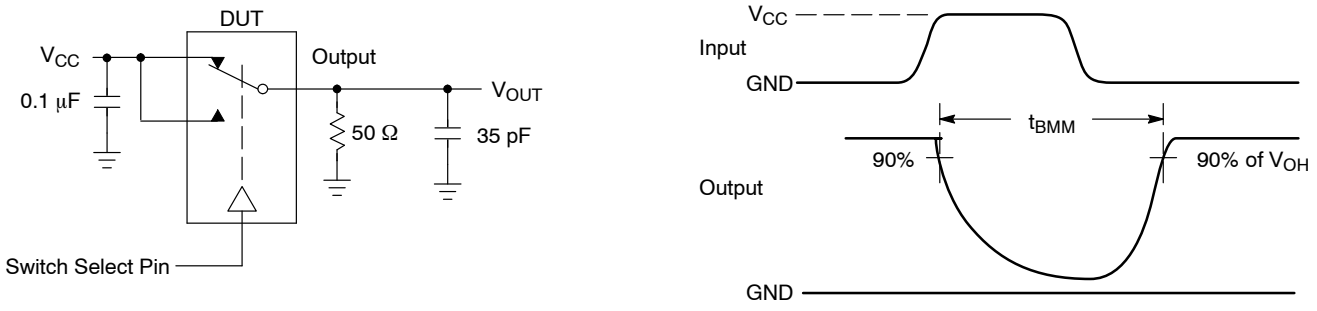


Figure 2. t_{BBM} (Time Break−Before−Make)

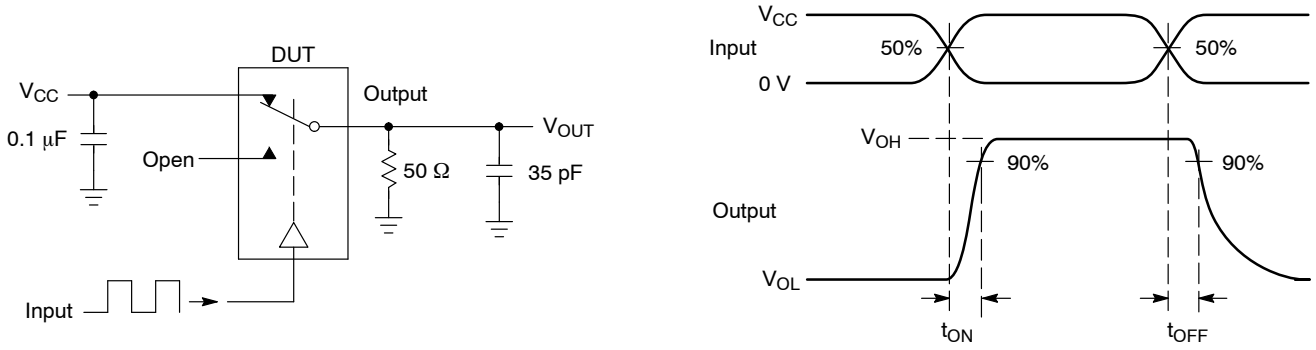


Figure 3. t_{ON}/t_{OFF}

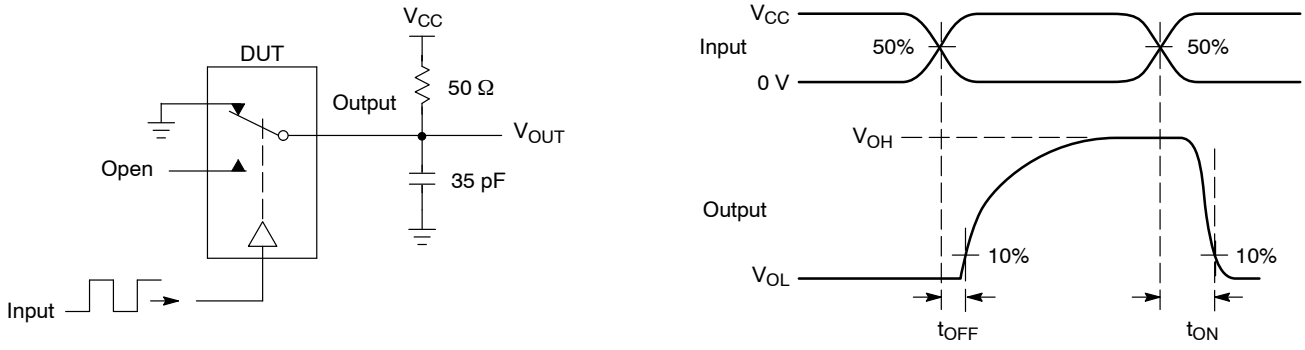
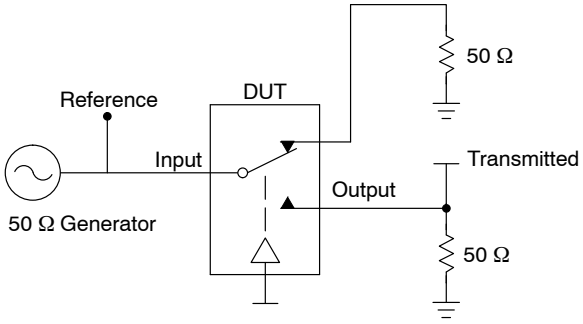


Figure 4. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO}, Bandwidth and V_{ONL} are independent of the input signal direction.

V_{ISO} = Off Channel Isolation = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz

V_{ONL} = On Channel Loss = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz to 50 MHz

Bandwidth (BW) = the frequency 3 dB below V_{ONL}
V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 5. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

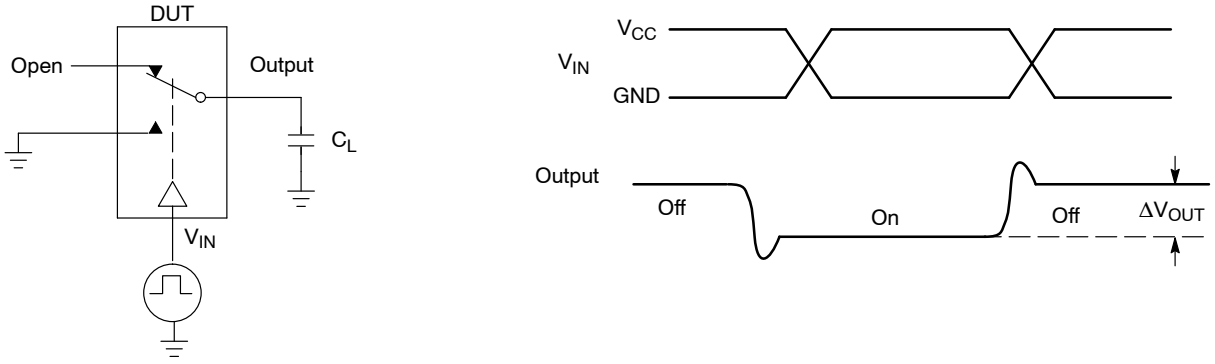


Figure 6. Charge Injection: (Q)

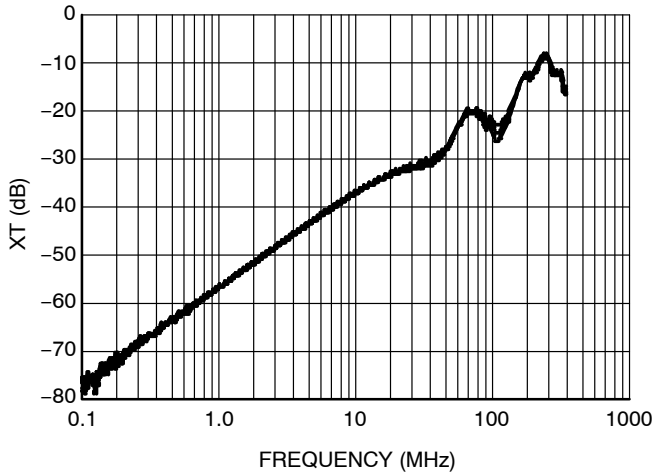


Figure 7. Cross Talk vs. Frequency @ V_{CC} = 4.5 V

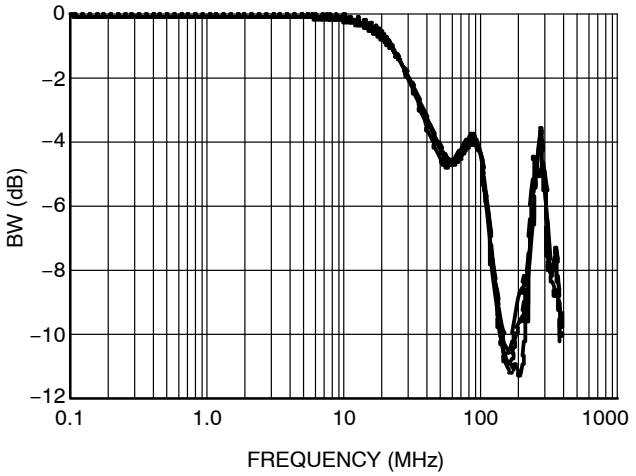


Figure 8. Bandwidth vs. Frequency

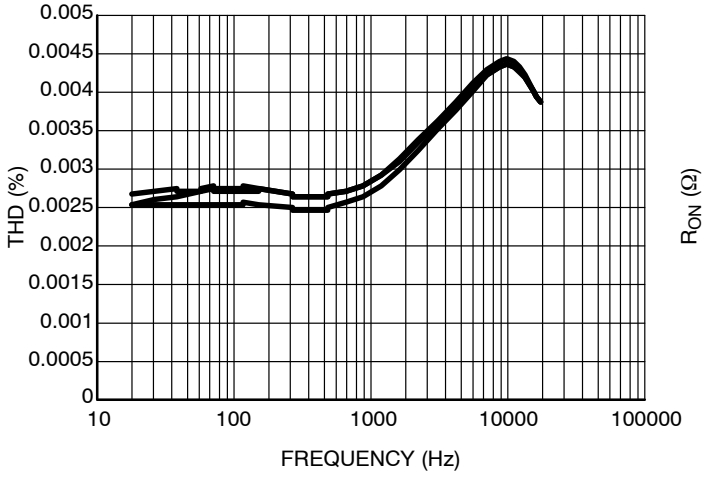


Figure 9. Total Harmonic Distortion

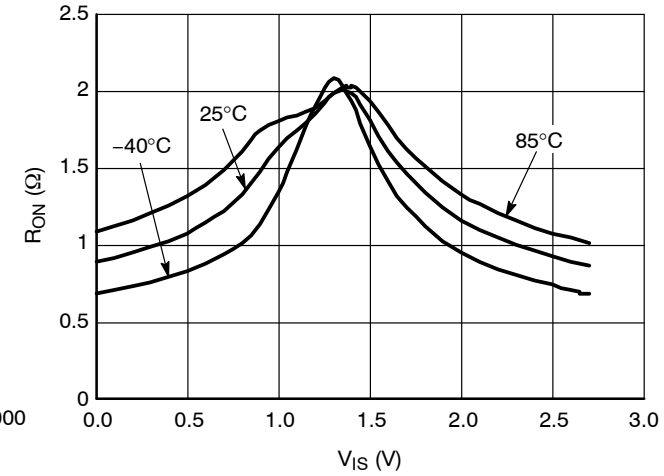


Figure 10. On−Resistance vs. Signal Voltage @ V_{CC} = 2.7 V

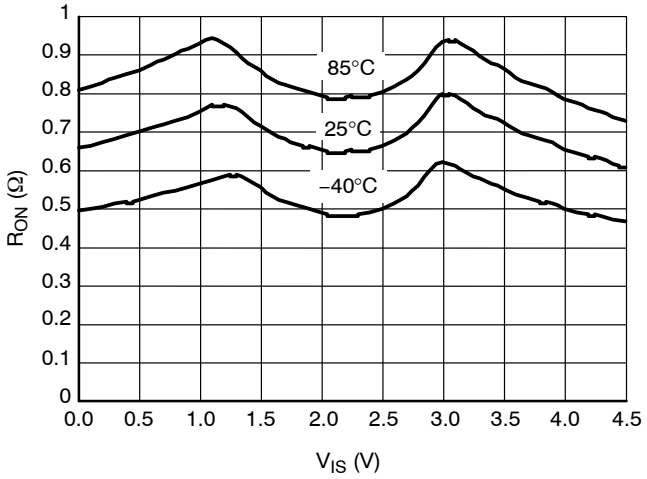


Figure 11. On−Resistance vs. Signal Voltage @ V_{CC} = 4.5 V

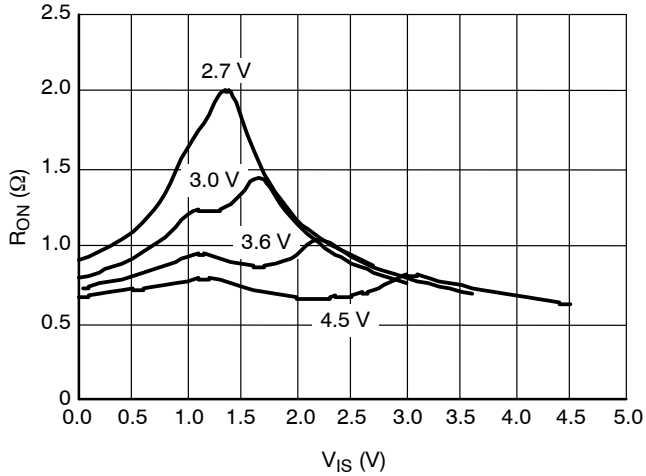
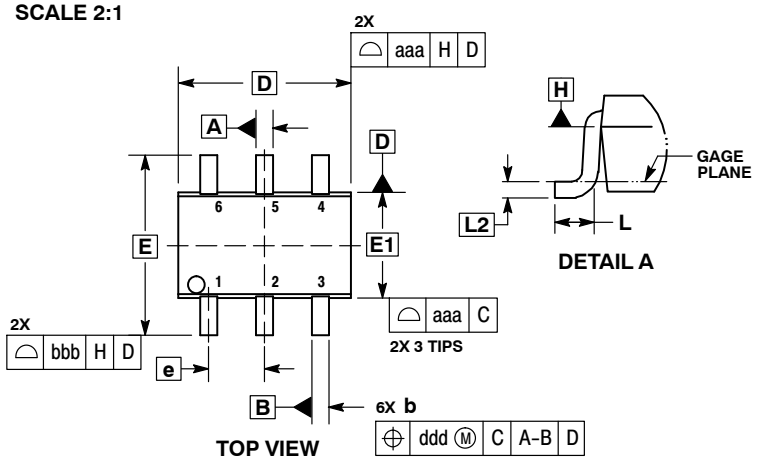


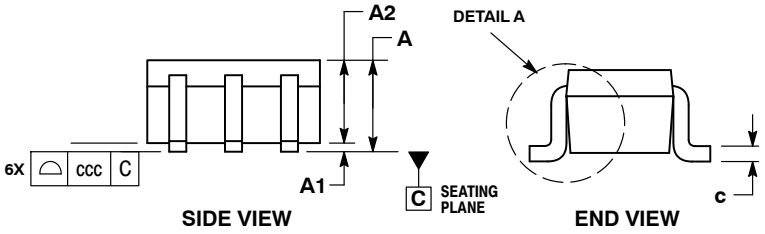
Figure 12. On−Resistance vs. Signal Voltage

SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

1
SCALE 2:1

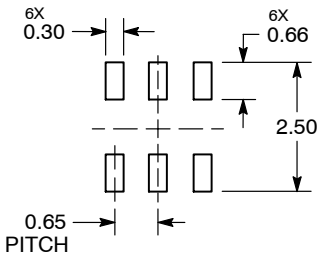




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	**MIN**	**NOM**	**MAX**	**MIN**	**NOM**	**MAX**
A	−−−	−−−	1.10	−−−	−−−	0.043
A1	0.00	−−−	0.10	0.000	−−−	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

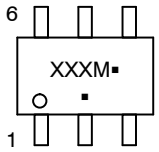
RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLES ON PAGE 2

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CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
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Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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